Low - eld di usion magneto-therm opower of a high mobility two-dimensional electron

gas

S. Maxim ov, M. Gbordzoe, H. Buhm ann and L. W. Molenkam p Physikalisches Institut (EP3), Universitat Wurzburg, Am Hubland, 97074 Wurzburg, Germany

D.Reuter

Lehrstuhl fur Festkorperphysik, Ruhr-Universitat Bochum, Universitatstr. 150, 44801 Bochum, Germany (Dated: April 14, 2024)

The low magnetic eld di usion them opower of a high mobility GaAs-heterostructure has been measured directly on an electrostatically de ned micron-scale Hall-bar structure (4 m 8 m) at low temperature (T = 1.6 K) in the low magnetic eld regime (B 1.2 T) where delocalized quantum Hall states do not in uence the measurements. The sample design allowed the determination of the eld dependence of the them opower both parallel and perpendicular to the temperature gradient, denoted respectively by S_{xx} (longitudinal therm opower) and S_{yx} (N emst-Ettinghausen coe cient). The experimental data show clear oscillations in S $_{xx}$ and S_{yx} due to the formation of Landau levels for 0.3 T < B 1.2 T and reveal that S_{yx} 120 S_{xx} at a magnetic eld of 1 T, which agrees well with the theoretical prediction that the ratio of these tensor components is dependent on the carrier mobility: $S_{yx} = S_{xx} = 2!_c$.

Keywords: Therm celectric e ect, magnetotransport PACS Numbers: 7220-i, 7220Pa, 7220Fr

Therm opower experiments have been used extensively to obtain inform ation on transport and scattering in twodim ensional electron gases (2DEGs) in compound sem iconductors (for reviews, see Refs. [1] and [2]). Because of the strong electron phonon coupling in these system s, the experim ental signal is usually dom inated by phonondrag, hence, apart from the desired electronic transport contributions, the signal also contains a very signi cant contribution due to details of the electron-phonon interaction. In order to extract the true electronic or \di usion" therm opower, usually drastic approxim ations have to be made [1, 2]. It would thus be very desirable to have an experim ental approach that is not in uenced by phonon-drage ects and directly yields the di usion therm opower. In this paper we describe the developm ent of such an experim ent.

W e present direct m easurem ents of the m agnetic eld dependence of the di usion therm opower using current heating techniques in specially designed m icro-H all bar structures. The samples were fabricated from high mobility G aA s-A IG aA s heterostructures [$100 \text{ m}^2 / (V \text{ s})$] using split-gate techniques. A current passing through an electron channel adjoining the Hall structure is used to exclusively heat the electron gas, leaving the lattice tem perature unchanged. This current-heating technique has previously been successfully used to determ ine the di usion therm opower of mesoscopic systems such as quantum point contacts [3] and quantum dots [4, 5, 6]. The present sample design allows the direct measurement of the tensor components of the therm opower both parallel (S_{xx}) and perpendicular (S_{yx}) to the tem perature gradient in x-direction. The results are discussed in the fram ework of theoretical models developed for the magnetic eld regim e where the form ation of Landau levels leads to a modulation of the density of states [7], but does not yet induce the form ation of edge states. Therefore, the magnetic eld in the present study is restricted to the low eld regim e (B 12 T) where the in uence of the quantum Halle ect can be neglected.

Fig. 1 shows an SEM -photograph of the sam ple structure, including a schematic diagram of the measurement. The micro-Hall bar and the electron heating channel are de ned by Schottky-gates, thus form ing the quantum point contacts (QPCs), which are used as voltage probes. Gates A, D, E and F form the micro-Hallbar and gates A, B, C and D the heating channel. Utilizing the fact that the therm opower of a QPC is quantized [3], QPC_4 and QPC_5 are used to determ ine the electron temperature in the channel T_{ch} by measuring the V₅ V₂ across the electron chanvoltage drop V_{25} nel, while gates E and F are not de ned. W e then have $V_{25} = (S_{QPC5} \quad S_{QPC4}) T_{ch}$, where T_{ch} equals the tem perature di erence between the electrons in the channel (T_{ch}) and in the surrounding 2DEG (T_1 1:6 K), which is in therm al equilibrium with the crystal lattice: $T_{ch} = T_{ch}$ T_1 [8]. Note that the tem perature difference T_{ch} enters here rather than a gradient, since the therm ovoltage across a QPC can only be measured globally. Experimentally, one observes that T_{ch} / I^2 , where I is the net heating current, as expected from a simple heat balance equation that is valid for not too large current values [9]. Fig. 2 shows the experimentally determ ined therm ovoltage as a function of the channel heating current. It can be seen that the parabolic dependence is valid for currents up to 12 A.For the tem perature calibration the therm opower of QPC4 was adjusted

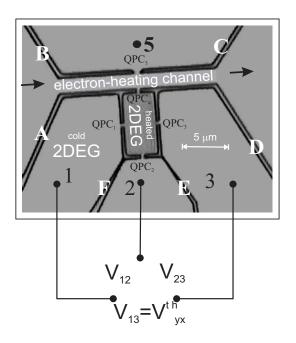


FIG .1: SEM -photograph of the split-gates structure and the scheme of the measurements.

to $S_{QPC4} = 20 V/K$ [9] and the therm opower of QPC 5 was set at a minimal value (S_{QPC5} 0). The temperature calibration is given on the right axis of Fig. 2.

For a therm opower experim ent on the m icro-H all bar, QPC_4 was adjusted into the tunneling regime (G_{OPC4} 3 10 ⁵ $^{1} < e^{2} = h$). QPC₁, QPC₂ and QPC₃ were set to higher conductance values (G_{OPC} 10 $2e^2=h$) in order to keep their therm op ower m in in al $(S_{QPC1;2;3})$ 0). The channel current was set to 10 A which yields an electron tem perature in the channel of T_{ch} 6:6 K [c.f. Fig. 2]; this current value gave a good com prom ise between pronounced therm ovoltage signals and the avoidance of lattice heating e ects. The inset of Fig. 2 shows the longitudinal resistance of the channel at this current level of 10 A; evidently the Shubnikov-de H aas oscillations are nearly suppressed, which ensures an approxin ately constant heat dissipation over the eld range studied.

The experiments were carried out at a temperature of about 1.6 K in an ⁴He cryostat equipped with a 10 T superconducting magnet. The 2DEG carrier density (2.8 10^{15} m²) and mobility ($100 \text{ m}^2 (\text{Vs})^{-1}$) were obtained from Hall and Shubnikov-de Haas (SdH) measurements. Standard lock-in amplier measurement techniques were used to measure the therm oelectric effects. As mentioned above, the 2DEG heating is proportional to I². Using ac-currents (I = i₀ cos(!t)) and a lock-in detection of the second harmonic (2!), the measured signal solely depends on the therm ovoltage [V_{th} / I² = (i₀ cos(!t))² / i₀² cos(2!t)].

Fig. 1 indicates how the two tensor components of the

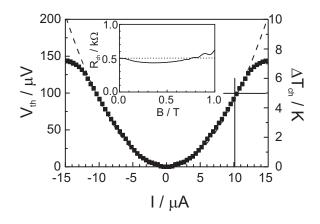


FIG.2: Electron temperature as a function of the channel heating current. The solid line with squares represents the m easured data; the dotted line is a parabolic t. Inset: Suppression of the SdH oscillations in the channel at a heating current of 10 A. The di erence between the dotted line and the m inimum of the SdH is about 15%.

therm opower can be obtained in our current heating experiment. First, we note that the therm opower of a 2 DEG in a magnetic eld is a local property, so that the therm ovoltages we measure are proportional to a tem perature gradient, $V_{th} = Sr_x T dx$. We assume that the tem perature gradient across the micro-Hall bar coincides with the line 4-2 connecting QPC_4 and QPC_2 de ning the x-direction. An important parameter for the experim ent is the electron tem perature at the crossing of line 4-2 and the line connecting QPC_1 and QPC_3 (line 1-3 de ning the y-direction). If the electron tem perature outside the micro-Hall bar is assumed to be equal to the lattice tem perature, a tem perature gradient is expected to develop between the side which is in contact with the heating channel (T_e^{max} $\ensuremath{\mathtt{T}_{ch}}\xspace$) and the surrounding $2D \in G$ (T₁). In zero order approximation a constant tem perature gradient along the line connecting QPC_2 and QPC_4 would have the following form : $r_x T_e = (T_e^{max} T_1) = x_0$ 5 K = 8 m = 0.625 K / mwhere x_0 is the extension of the micro-Hall bar in xdirection $(x_0 = 8 \text{ m})$.

From Fig. 1, it is clear that $V_{yx}^{\,\rm th}$, the therm ovoltage perpendicular to the tem perature gradient, can be determined by measuring the voltage di erence between the areas1 and 3, V_{yx}^{th} V_{13} V_3 V_1 , provided the intrinsic therm opower of QPC $_1$ and QPC $_3$ can be neglected. For Vth_{xx} however, the required voltage probe at the crossing point of the lines 1-3 and 4-2 is not available. Instead, we can obtain $V_{xx}^{\,\text{th}}$ from measuring the signals present at $V_2 = V_1$ and V_{32} $V_2 = V_3$. Since V_{12} and V_{23} V_{12} contain contributions from $\,V_{xx}^{\,th}\,$ as well as $V_{yx}^{\,th}$, $V_{xx}^{\,th}\,$ can be determ ined by adding V_{12} and V_{23} and subtracting $V_{yx}^{\,\rm th}$. This allows us to compare $V_{xx}^{\,\rm th}$ and $V_{yx}^{\,\rm th}$ di-V13 rectly without an exact know ledge of r x Te in the m icro-

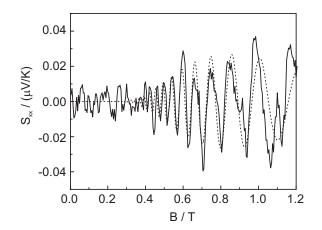


FIG.3: Them opower S_{xx} parallel to the tem perature gradient: The solid line corresponds to the experimental data for T = 2.5 K and the dashed dotted line represents the calculation according to Eq.3.

Hall structure.

For both components, the experiments show clear oscillations in the therm opower with magnetic eld (Figs. 3 and 4). The therm opower signal has been calculated from the therm ovoltage measurem ent assuming the linear tem perature gradient as m entioned above. The presented eld range studied can be separated into two parts: First, B < 0.3 T; the electrons are considered as classical particles which are de ected by the applied m aqnetic eld and scattered elastically at the device boundaries (mean free path 1_{m fp} 8 m) [10], and second, 0:3 < B < 1:2 T where the oscillations correspond to the form ation of Landau levels in the 2DEG and hence to the magnetic eld dependent modulation of the density of states. In the following, we will present a detailed quantitative discussion of the second magnetic eld regime (0:3 < B < 1:2 T).

A coording to Ref. [7] the magnetic eld behaviour of the therm opower oscillations can, in the regime of Landau level form ation, be described by the following equations:

$$S_{xx} = \frac{2}{1 + !_{c}^{2} 2} \frac{k_{B}}{e} D^{0}(X)$$

$$exp \quad \frac{2^{2}k_{B}T_{D}}{h!_{c}} \sin \frac{2f}{B}$$
(1)

$$S_{yx} = \frac{4!_{c}}{1 + !_{c}^{2} 2} \frac{k_{B}}{e} D^{0}(X)$$

$$exp \frac{2^{2}k_{B}T_{D}}{h!_{c}} \sin \frac{2f}{B}$$
(2)

where T_D is the D ingle tem perature, !_c the cyclotron frequency, the transport relaxation time, and f is the frequency of the oscillations (f=B = E_F=h!_c, where E_F

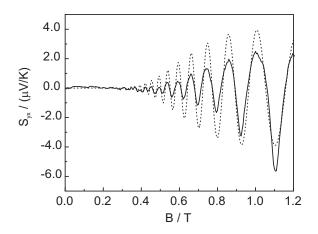


FIG.4: Them opower S_{yx} perpendicular to the tem perature gradient: The solid line corresponds to the experim ental data for T = 2.5 K and the dashed dotted line represents the calculation according to Eq.4.

is the Ferm i energy). The quantity D 0 (X) is the derivative of the therm al dam ping factor D (X), de ned by D (X) = X = sinh X where X = 2 $^2k_{\rm B}\,T=h!_{\rm c}$. These equations were originally [7] derived for conditions where $!_{\rm c}$ < 1, which would restrict the validity in our case to m agnetic elds up to B 20 mT. However, Coleridge et al. [12] have shown that Eqs. (3) and (4) are valid up to much higher eld values (B 1 T) when localization e ects can be neglected (as it is the case for high m obility 2D EG s).

The results of the m easurem ents up to 1.2 T are presented in Fig. 3 and Fig. 4 together with the using Eqns. (1) and (2). For the tes, the carrier density n and the mobility were taken from the transport characterization. The D ingle tem perature was obtained from the assumption that the quantum mobility is approximately 10 times lower than the electron mobility i.e. $T_D = 0.4 \text{ K} [7, 12]$. The thermal smearing was tted by a free parameter T_e , which can be interpreted as the average electron tem perature in the micro-H all bar. The best to for an average electron tem perature of $\overline{T}_e = 4 \text{ K}$ is in very good agreement with the estimates made above concerning the tem perature gradient.

Both S_{xx} and S_{yx} can be tted satisfactorily using the same set of parameters, even though the amplitudes are very dierent. According to Eqns. (3) and (4), the ratio of the therm opower perpendicular and parallel to the temperature gradient is given by $S_{yx}=S_{xx}=2!_{\rm c}$. For the present sample, the measured ratio at B=1T is 120. Again, this value agrees well with the expected value of 160. To our know ledge this is the rst successful measurement of the di usion therm opower for a sem iconductor 2DEG system. The current heating approach allow s us to avoid the in uence of phonon-drag e ects [7, 14, 15]. From the consistency of the average tem peratures and the tem perature gradients, which are obtained from the tting and the channel tem perature calibration, it can be concluded that the chosen geom etry and the measurement con guration are suitable for investigating the di usion therm opower of high mobility sam ples.

Sum marizing, the results presented here demonstrate that electron heating techniques can be used to measure directly the longitudinal and transverse components of the di usion therm opower. For low magnetic elds, thermopower uctuations are observed which originate from quasi-ballistic electrons; for higher elds, the modulation of the electron density of states due to Landau level formation determines the oscillatory part of the diusion therm opower. Current theories [2, 7] describe this oscillatory behavior to a large extent and can be used to independently gauge the electron tem perature. The consistency of these m easurem ents with theory opens up the way for an alternative m ethod for studying the di usion therm opower in the QHE as well as in the fractional quantum Halle ect regime, where currently, experim ental data are discussed controversially [1, 16, 17, 18].

This work performed with nancial support from the D eutsche Forschungsgemeinschaft (DFG M o 771/5-2).

- [1] R.Fletcher, Sem icond.Sci.Technol.Vol14,R1 (1999).
- [2] B L.G allagher and P N.Butcher, in H andbook on Sem iconductors, edited by P.T.Landsberg, (Elsevier, Amsterdam), Vol.1, p.817 (1992).
- [3] L.W. Molenkamp, H. van Houten, C.W. J. Beenakker, R. Eppenga, C.T. Foxon, Phys. Rev. Lett., 65 1052 (1990).

- [4] A A M . Staring, L W . M olenkamp, B W . A lphenaar, H. van Houten, O JA. Buyk, M A A. M abesoone, C W J. Beenakker, and C T. Foxon, Europhys. Lett. 22, 57 (1993).
- [5] S. Moller, H. Buhmann, S.F. Godijn, and L.W. Molenkamp, Phys. Rev. Lett., 81, 5197 (1998).
- [6] SF.Godin, S.Moller, H.Buhmann, LW. Molenkamp, and SA.van Langen, Phys. Rev. Lett., 82, 2927 (1999).
- [7] R.Fletcher, P.T. Coleridge and Y.Feng, Phys. Rev. B, 52 2823 (1995).
- [8] L.W. Molenkamp, H. van Houten, C.W. Beenakker, R. Eppenga and C.T. Foxon, Condensed System sofLow D imensionality, edited by JL. Beeby et al., Plenum Press, New York, p.335 (1991).
- [9] H. van Houten, LW. Molenkamp, CW J. Beenakker, and C.T. Foxon, Sem icond. Sci. Technol 7, B215 (1992).
- [10] For a qualitative and quantitative discussion of the low magnetic eld regime (0 B < 0.3 T) a detailed theoretical modelling of the ballistic therm opower of this special sample geometry is needed including a numerical calculation of the related transmission probabilities [11], which will be given in a later publication.
- [11] A.G. Pogosov, M.V. Budantsev, D.Uzur, A. Nogaret, A.E. Plotnikov, A.K. Bakarov, and A.J. Toropov, Phys. Rev. B 66, 201303R (2002).
- [12] P.T. Coleridge, R. Stoner, R. Fletcher, Phys. Rev. B, 39 1120 (1989).
- [13] G F. Giuliani and J.J. Quinn, Phys. Rev. B 26 4421 (1982).
- [14] R.Fletcher, V M.Pudalov, Y.Feng, M.Tsaousidou, PN. Butcher, Phys. Rev. B, 56, 12422, (1997).
- [15] R.Fletcher, V M Pudalov and S.Cao, Phys. Rev. B 57, 7174, (1998).
- [16] B. Tieke, R. Fletcher, U. Zeitler, M. Henini and J.C. Maan, Phys. Rev. B 58, 2017 (1999).
- [17] X.Ying, V.Bayot, M.B.Santos and M.Shayegan, Phys. Rev.B 50, 4969, (1994).
- [18] D.V.Khveshchenko, Phys.Rev.B, 54, R14317, (1996).